

## 18A, 600V N-CHANNEL MOSFET

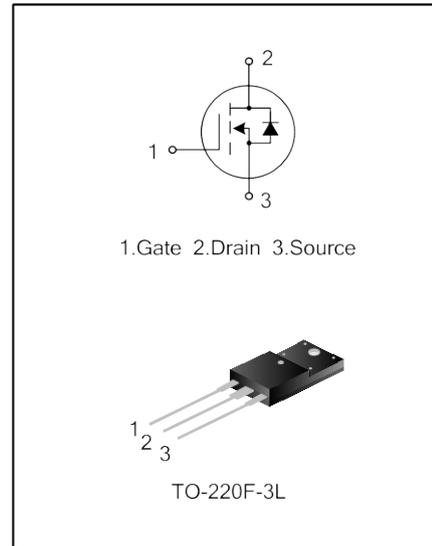
### GENERAL DESCRIPTION

SVF18N60F is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ structure VDMOS technology. The improved planar stripe cell and the improved guarding ring terminal have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

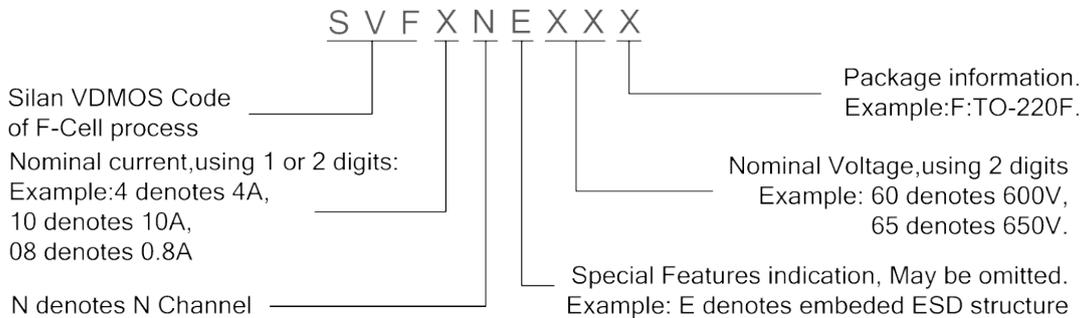
These devices are widely used in AC-DC power suppliers, DC-DC converters and H-bridge PWM motor drivers.

### FEATURES

- \* 18A,600V, $R_{DS(on)}$  (typ) =0.36Ω@V<sub>GS</sub>=10V
- \* Low gate charge
- \* Low Crss
- \* Fast switching
- \* Improved dv/dt capability



### NOMENCLATURE



### ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SVF18N60F	TO-220F-3L	SVF18N60F	Pb free	Tube